

IN THE CLAIMS:

Claims 1-14 have been amended herein. All of the pending claims 1 through 14 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method of fabricating an interposer substrate for attaching to an active surface of a semiconductor die having a plurality of conductive bumps protruding transversely therefrom, the method comprising:
providing a substrate having a first surface and a second surface, ~~said the~~ substrate including a dielectric layer and a plurality of conductive elements on ~~said the~~ dielectric layer adjacent ~~said the~~ second surface; and
forming a plurality of recesses in ~~said the~~ first surface of ~~said the~~ substrate and through ~~said the~~ dielectric layer to a depth through ~~said the~~ dielectric ~~layer~~ layer, each of the plurality of recesses ~~exposing to expose~~ at least a portion of a contiguous conductive element adjacent ~~said the~~ second surface and of a size and configuration to receive ~~said the~~ plurality of conductive bumps of ~~said the~~ semiconductor die so that ~~said the~~ plurality of conductive bumps is substantially received within ~~said the~~ plurality of recesses.

2. (Currently Amended) The method of claim 1, wherein ~~said forming~~ ~~said the~~ plurality of recesses comprises forming ~~said the~~ plurality of recesses to a depth so that a surface of each of ~~said the~~ plurality of conductive bumps will contact ~~at the at~~ least a portion of a ~~said the~~ contiguous conductive element with ~~said the~~ active surface of ~~said the~~ semiconductor die abutting ~~said the~~ first surface of ~~said the~~ substrate.

3. (Currently Amended) The method of claim 1, further comprising forming at least one opening in ~~said the~~ second surface of ~~said the~~ substrate in communication with at least one recess of ~~said the~~ plurality of recesses.

4. (Currently Amended) The method of claim 1, wherein ~~said~~ providing ~~said~~ the substrate comprises forming ~~said~~ the plurality of conductive elements by at least one of printing conductive ink and etching a conductive layer.

5. (Currently Amended) The method of claim 1, wherein ~~said~~ providing ~~said~~ the substrate comprises disposing a solder mask over ~~said~~ the plurality of conductive elements in a pattern leaving portions of ~~said~~ the plurality of conductive elements exposed.

6. (Currently Amended) The method of claim 1, wherein ~~said~~ providing the substrate comprises providing ~~said~~ the dielectric layer as a flexible polymer material.

7. (Currently Amended) The method of claim 1, wherein ~~said~~ providing the substrate comprises providing ~~said~~ the substrate to include at least one of BT, FR4 laminate, FR5 laminate and UPILEX®.

8. (Currently Amended) The method of claim 1, wherein ~~said~~ forming ~~said~~ the plurality of recesses comprises collectively configuring ~~said~~ the plurality of recesses in a centrally aligned row in ~~said~~ the substrate to correspond with a conductive bump configuration on ~~said~~ the semiconductor die.

9. (Currently Amended) The method of claim 1, wherein ~~said~~ forming ~~said~~ the plurality of recesses comprises collectively configuring ~~said~~ the plurality of recesses in a peripheral configuration in ~~said~~ the substrate to correspond with a conductive bump configuration on ~~said~~ the semiconductor die.

10. (Currently Amended) The method of claim 1, wherein ~~said-forming-said the~~ plurality of recesses comprises collectively configuring ~~said the plurality of~~ recesses in an I-shaped configuration in ~~said the~~ substrate to correspond with a bump configuration on ~~said the~~ semiconductor die.

11. (Currently Amended) The method of claim 1, wherein ~~said-forming-said the~~ plurality of recesses comprises forming ~~said the~~ plurality of recesses by at least one of a wet etch, dry etch, mechanical drilling, mechanical punching and laser ablation.

12. (Currently Amended) The method of claim 1, wherein ~~said-forming-said the~~ plurality of recesses comprises patterning ~~said the~~ plurality of recesses, each substantially with a peripheral shape including at least one of a square, rectangle, circle and oval.

13. (Currently Amended) The method of claim 1, wherein ~~said-forming-said the~~ plurality of recesses comprises forming at least one sloped side wall in each of ~~said the~~ plurality of recesses.

14. (Currently Amended) The method of claim 1, wherein ~~said-forming-said the~~ plurality of recesses comprises forming at least one side wall in each of ~~said the~~ plurality of recesses to be substantially ~~normal~~ perpendicular with ~~said respect to the~~ first surface of ~~said the~~ substrate.